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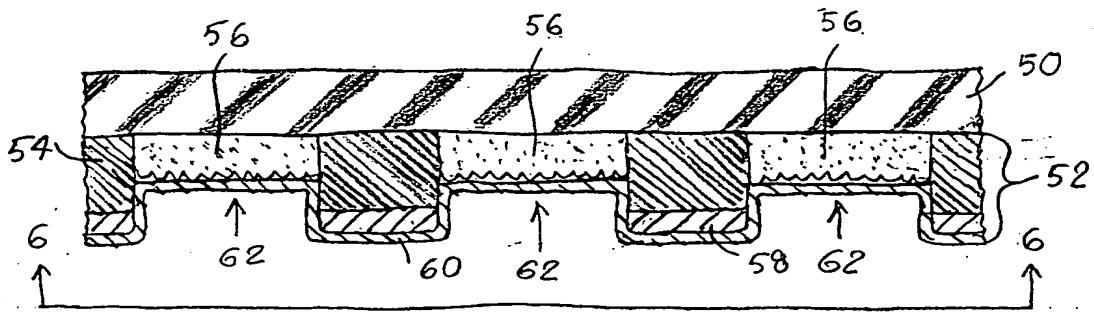


Fig. 5

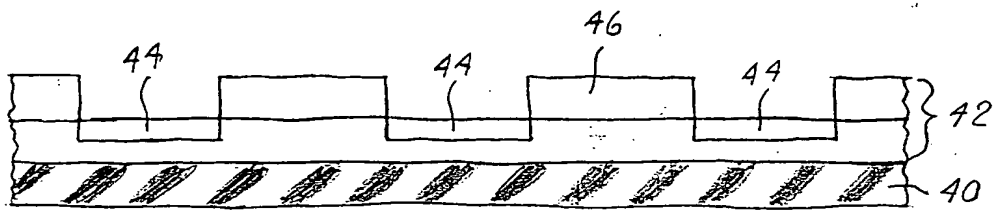
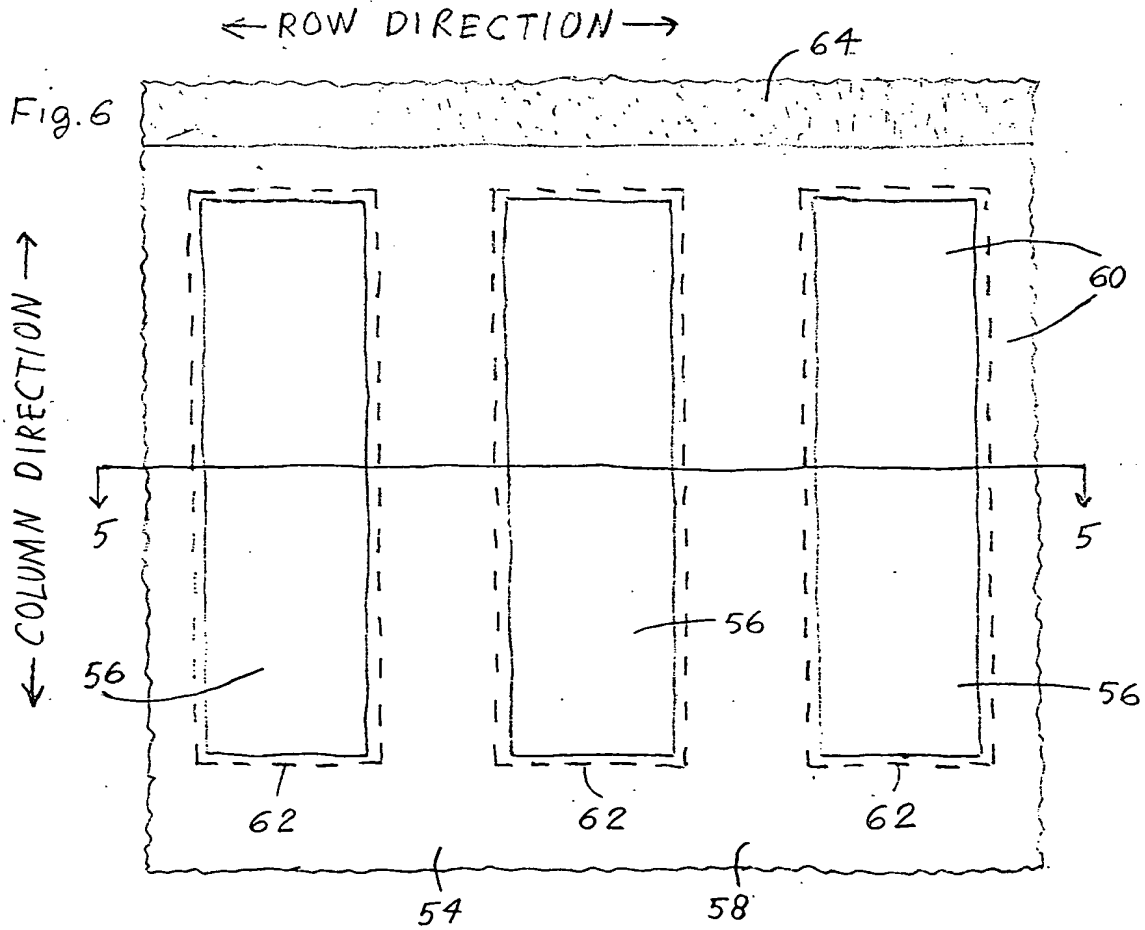


Fig. 6



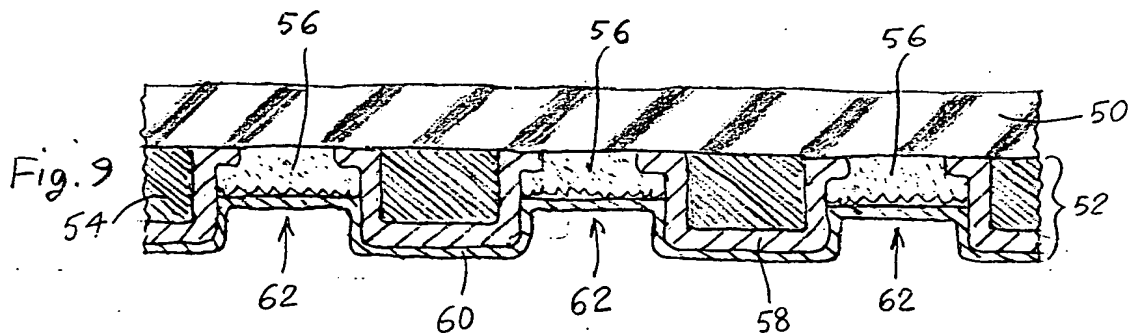
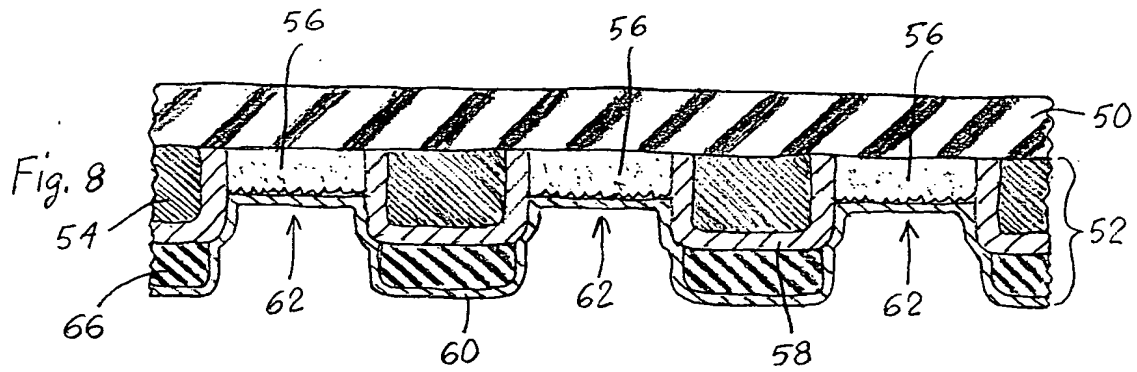
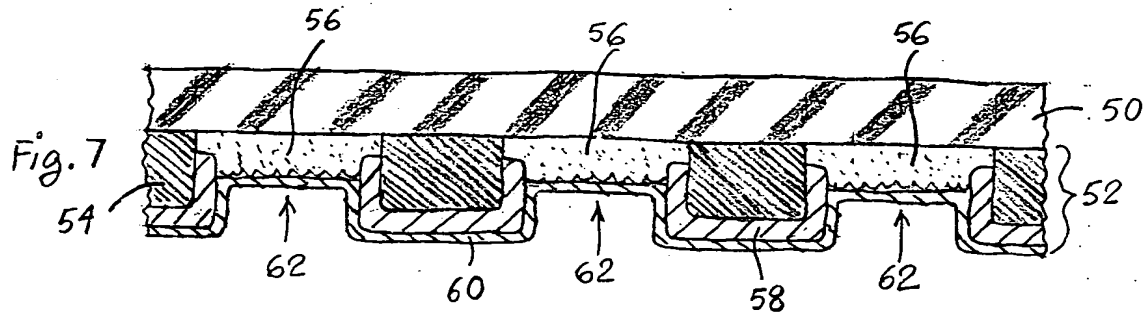


Fig.
10a

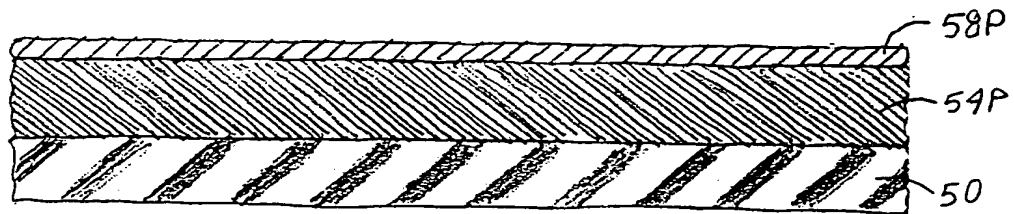


Fig.
10b

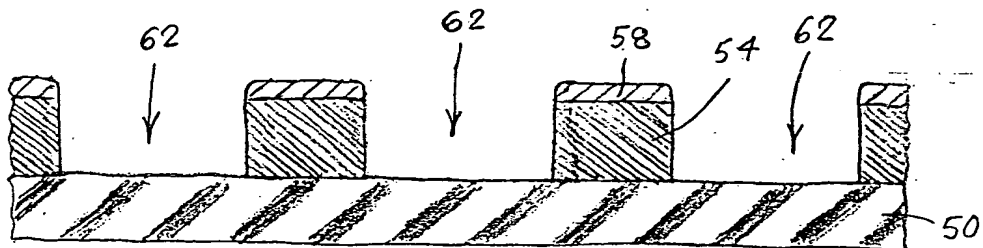


Fig.
10c

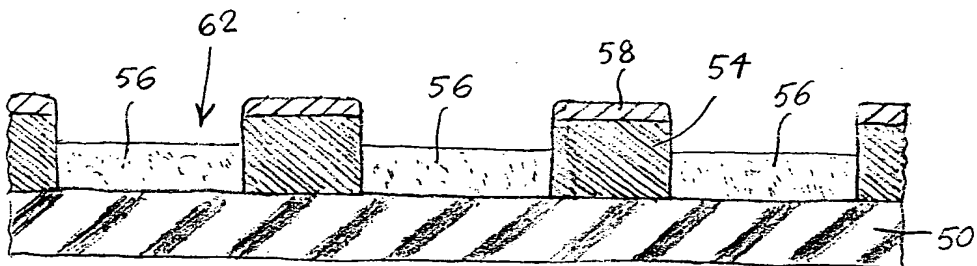


Fig.
1.0d

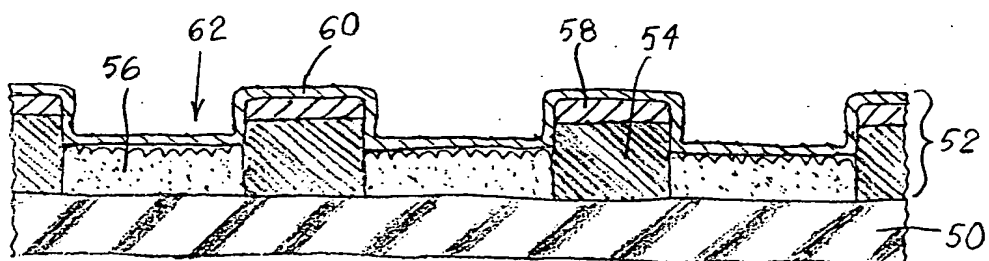


Fig. 11a

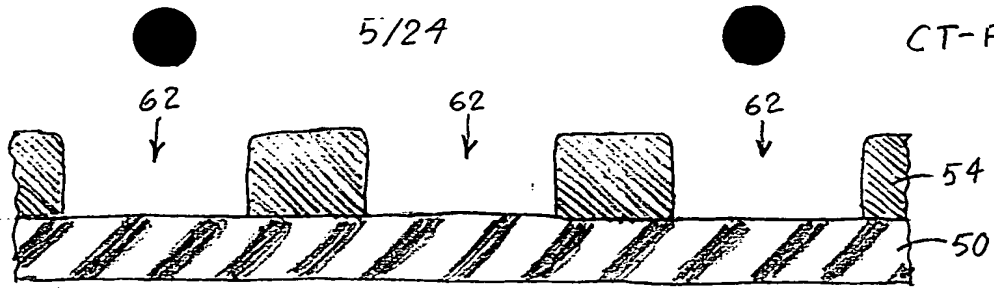


Fig. 11b

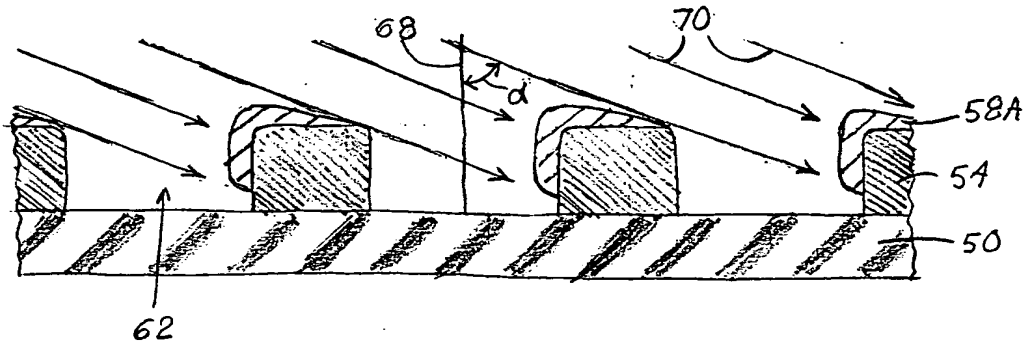


Fig. 11c

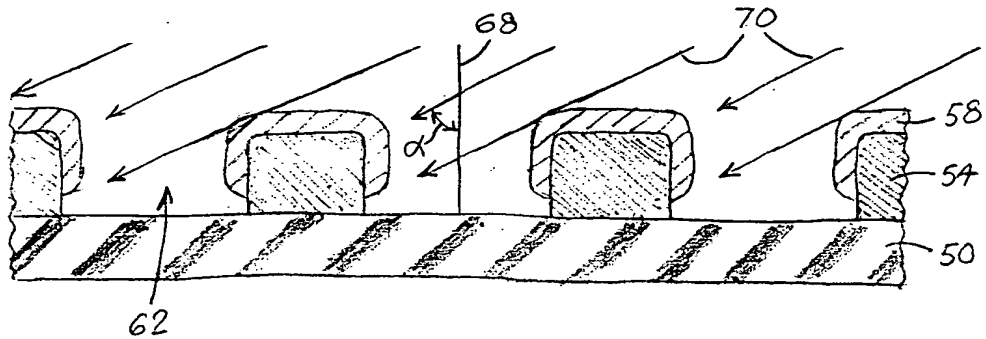


Fig. 11d

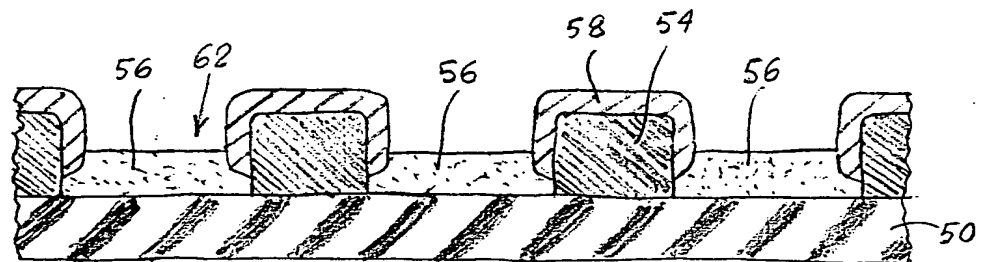
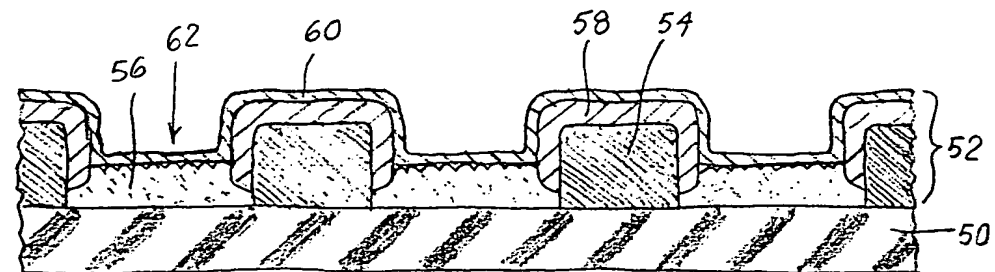


Fig. 11e



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Fig.
12a

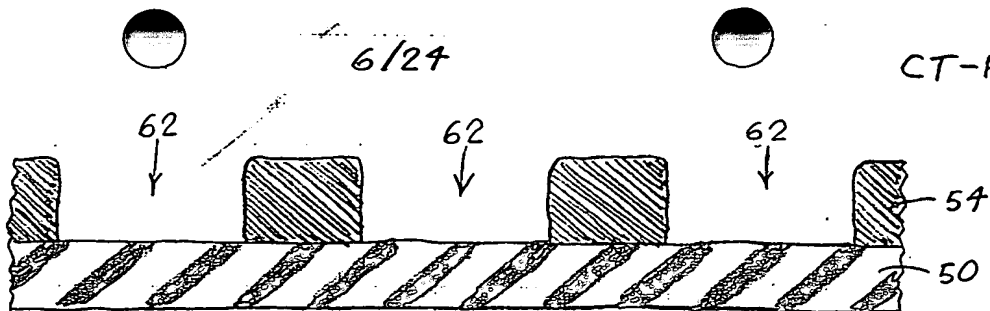


Fig.
12b

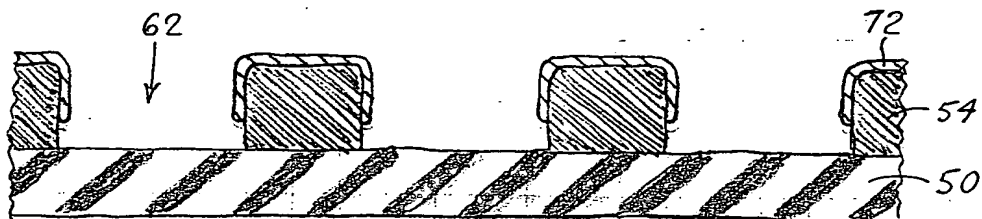


Fig.
12c

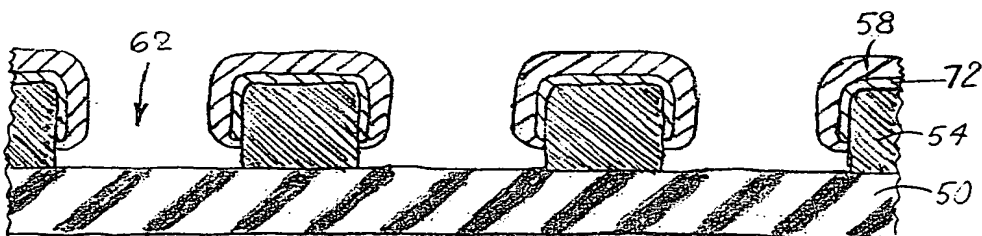


Fig.
12d

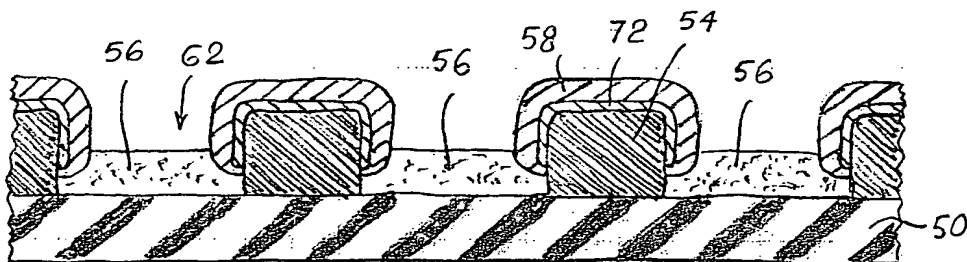
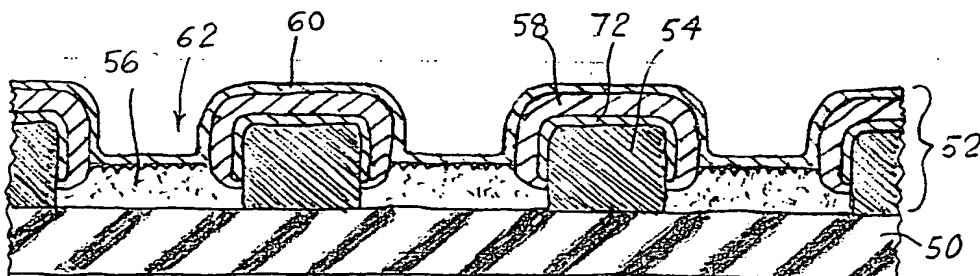
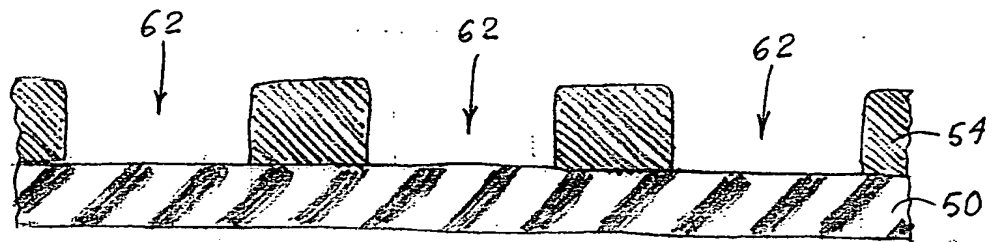
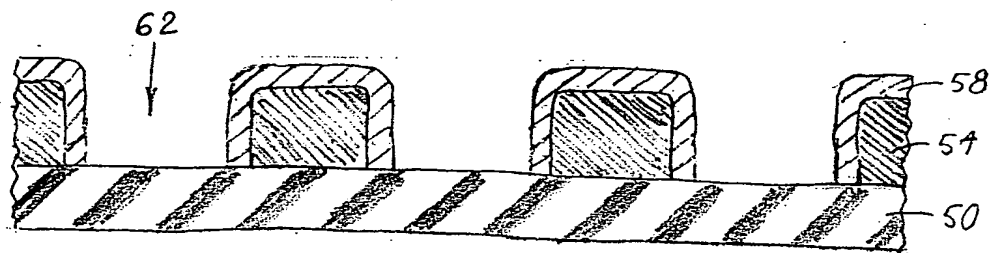
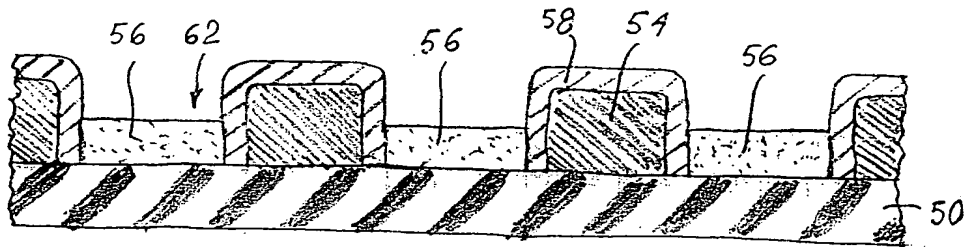
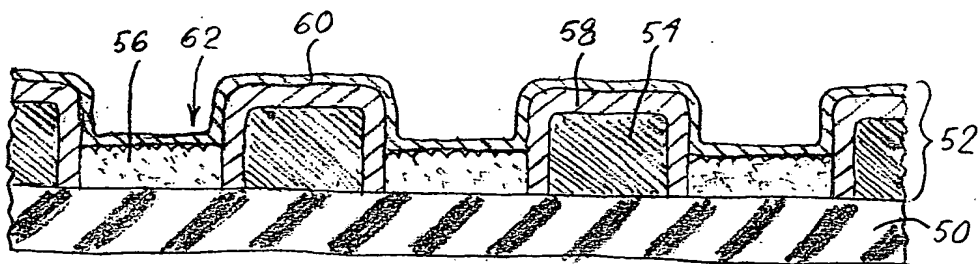


Fig.
12e



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Fig.
13aFig.
13bFig.
13cFig.
13d

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Fig.
14a

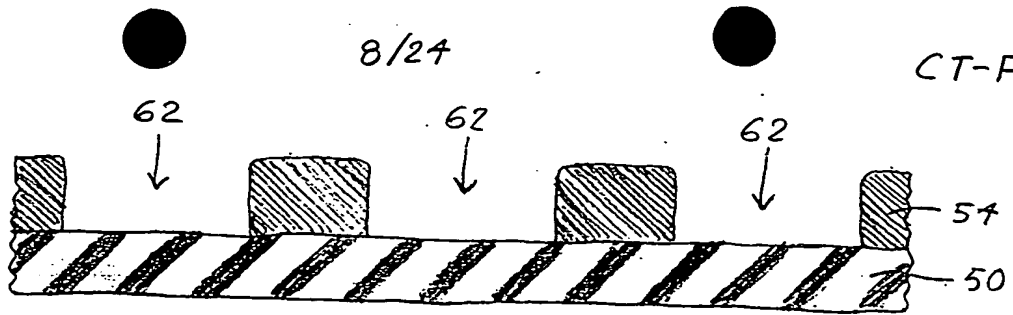


Fig.
14b

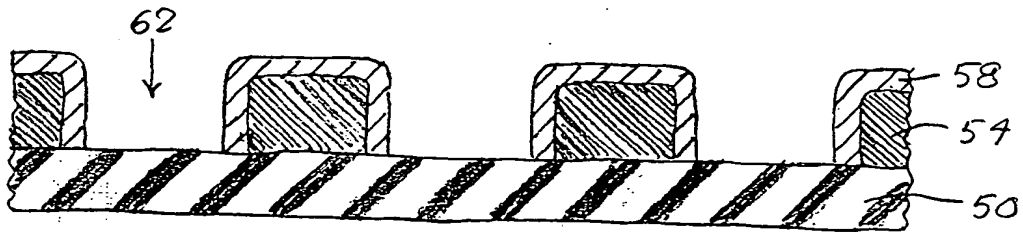


Fig.
14c

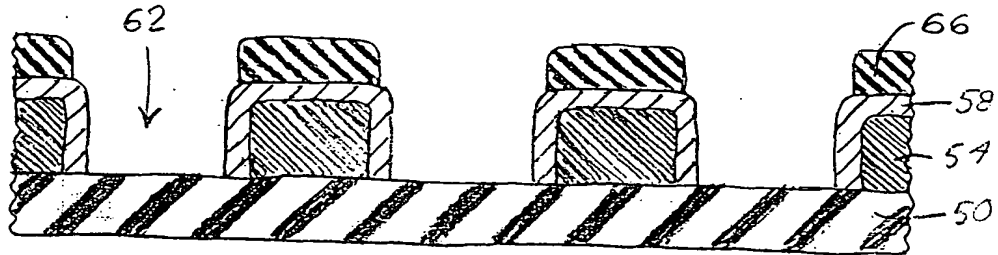


Fig.
14d

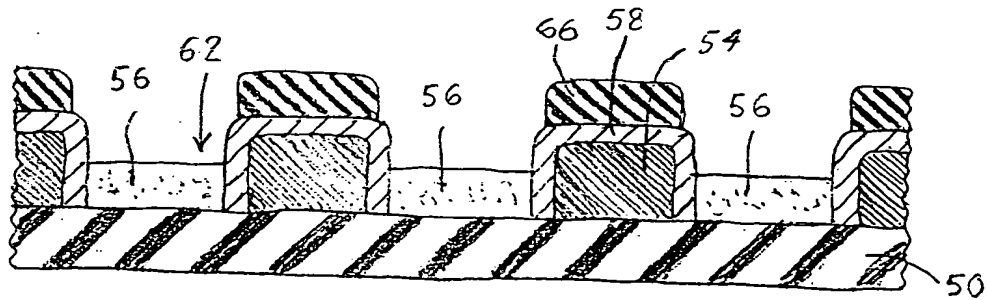
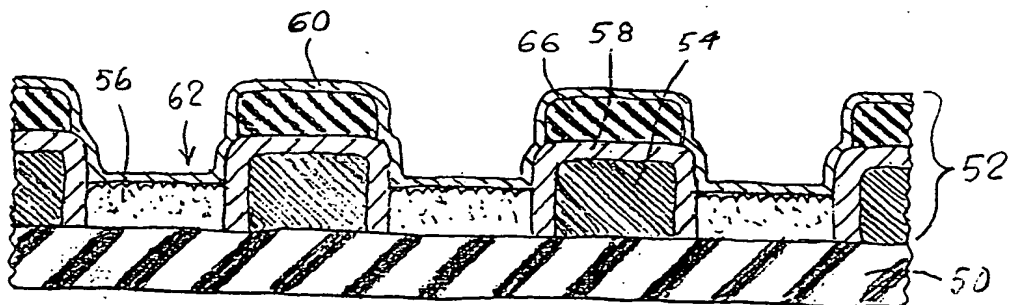
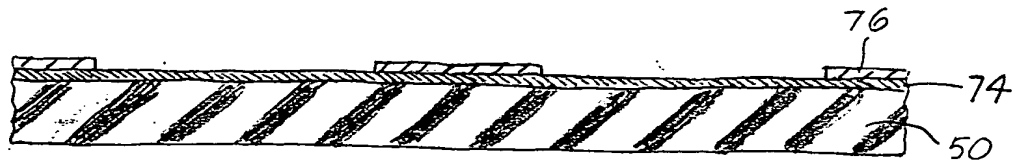
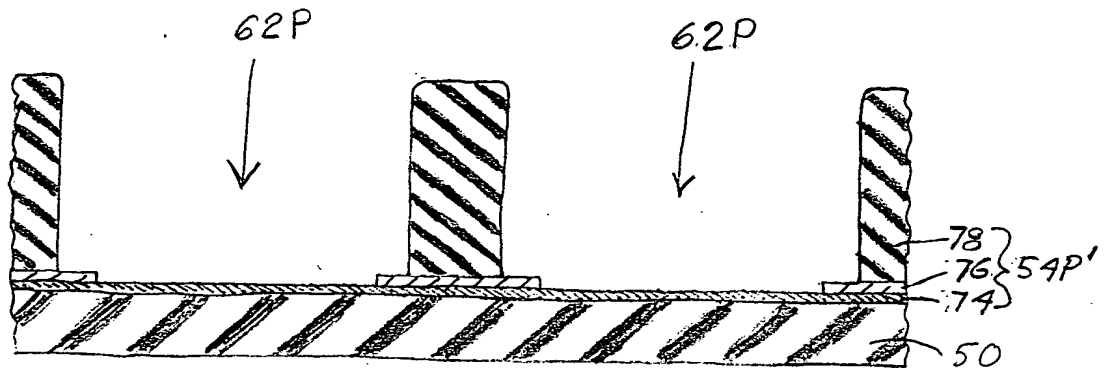
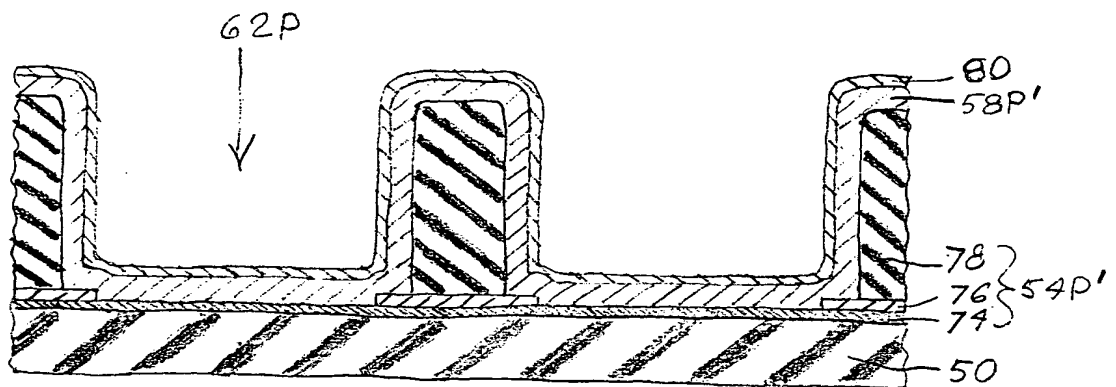
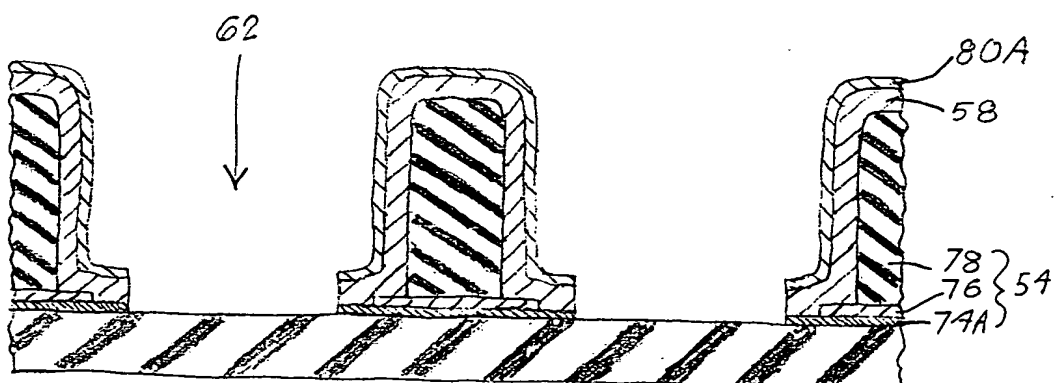


Fig.
14e



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Fig.
15aFig.
15bFig.
15cFig.
15d

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Fig.
15e

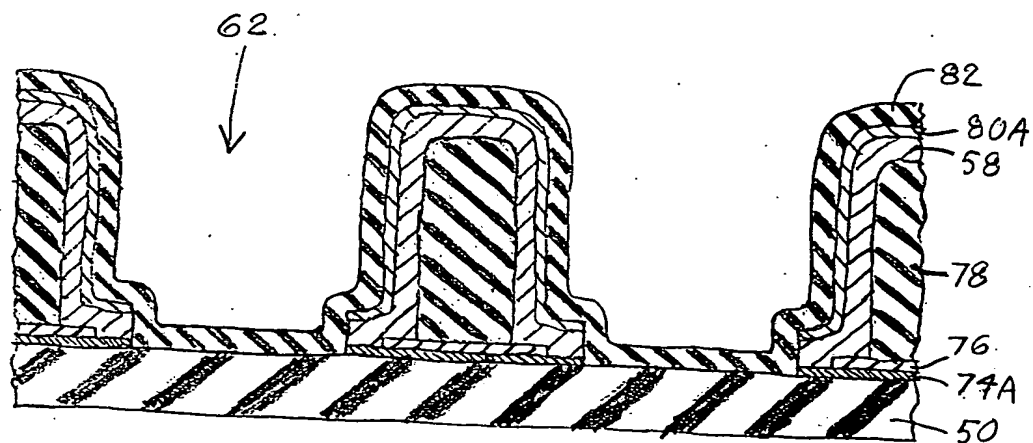


Fig.
15f

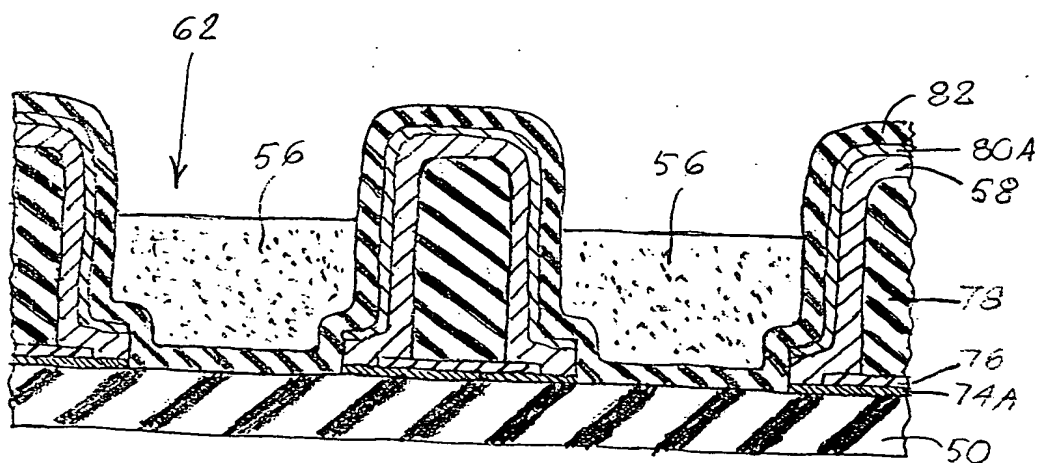
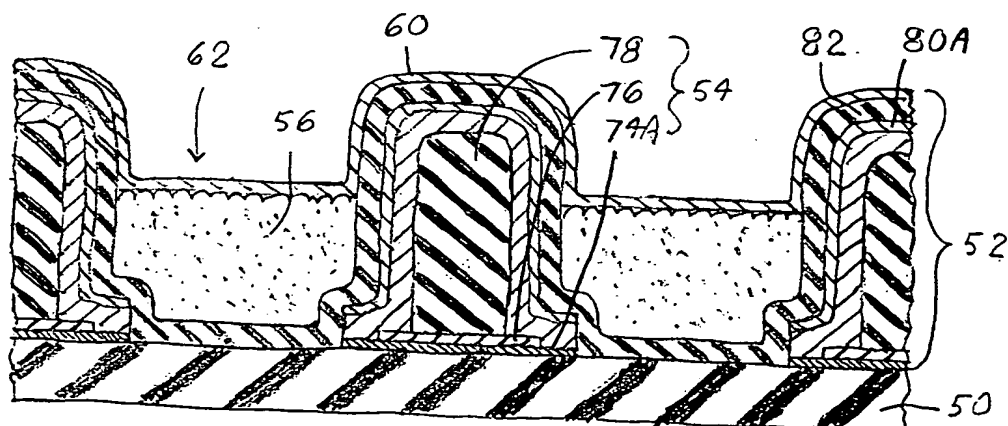


Fig.
15g



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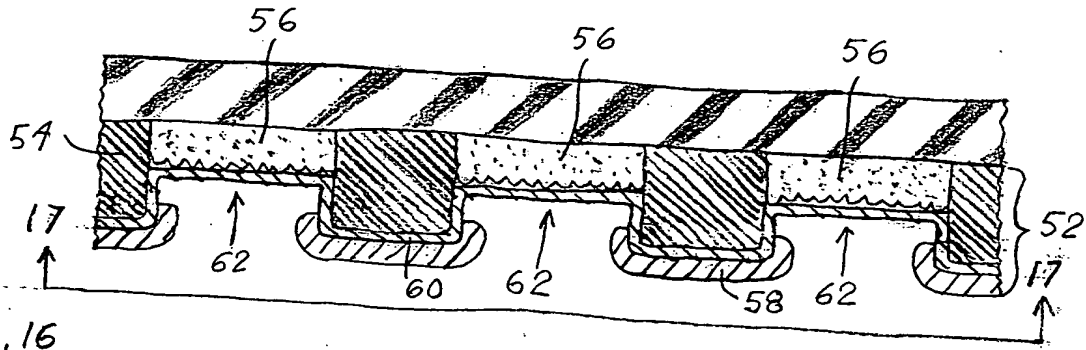
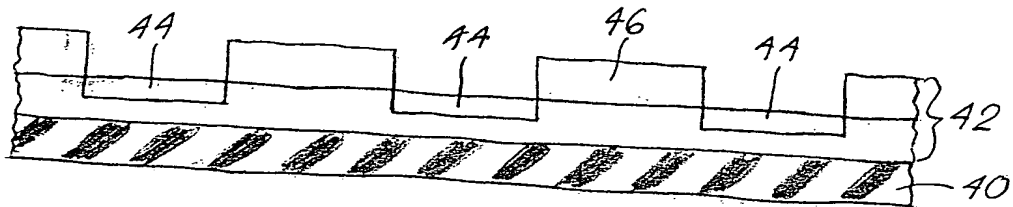


Fig. 16



← ROW DIRECTION →

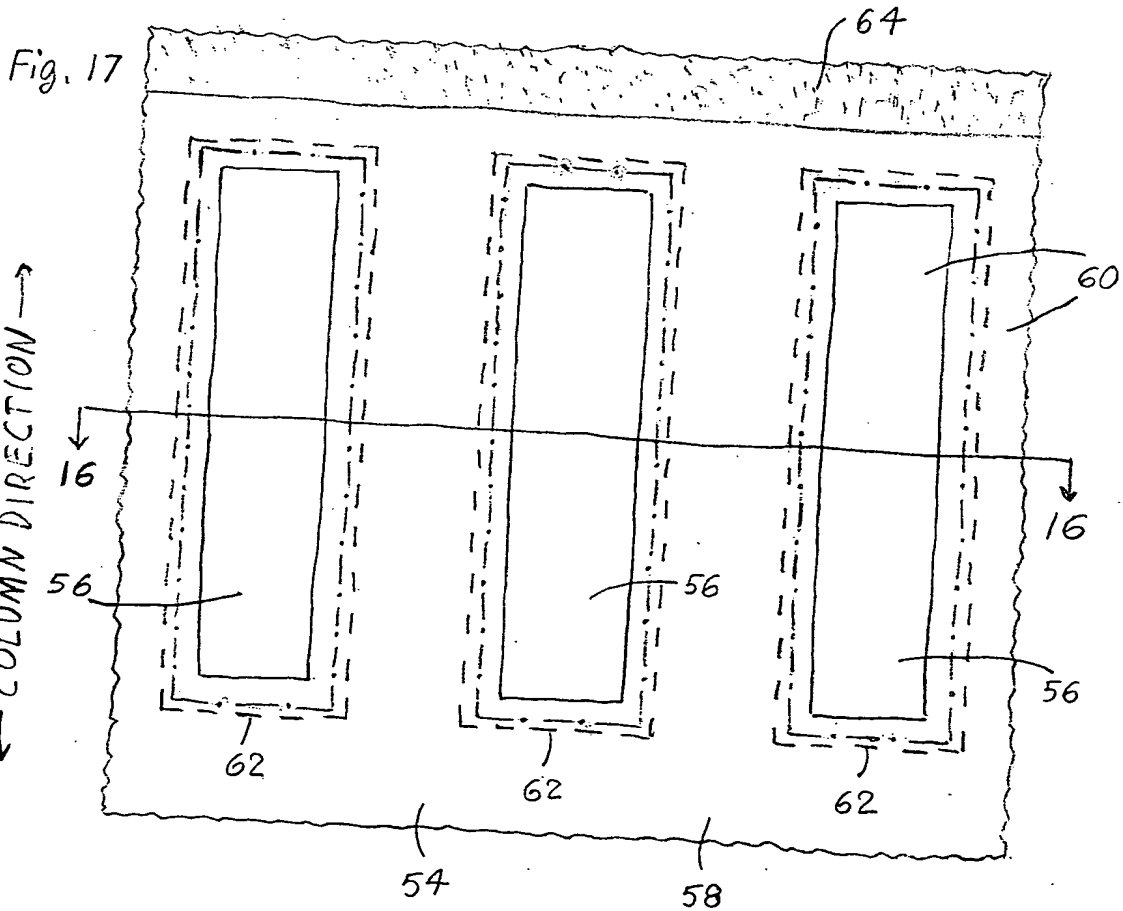


Fig. 17

← COLUMN DIRECTION →

Fig. 18a

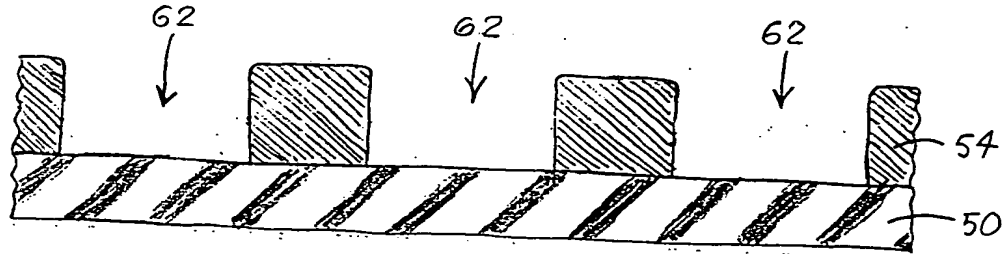


Fig. 18b

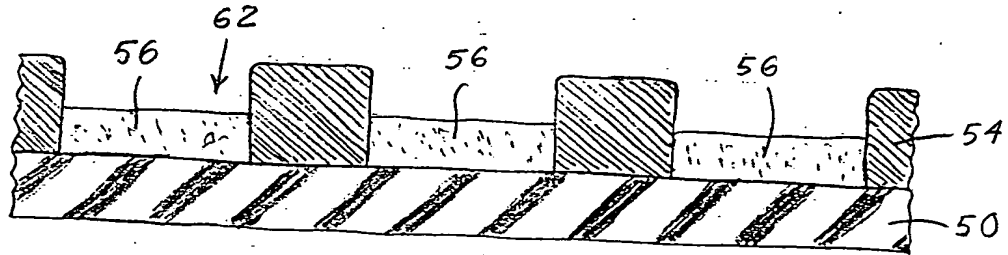


Fig. 18c

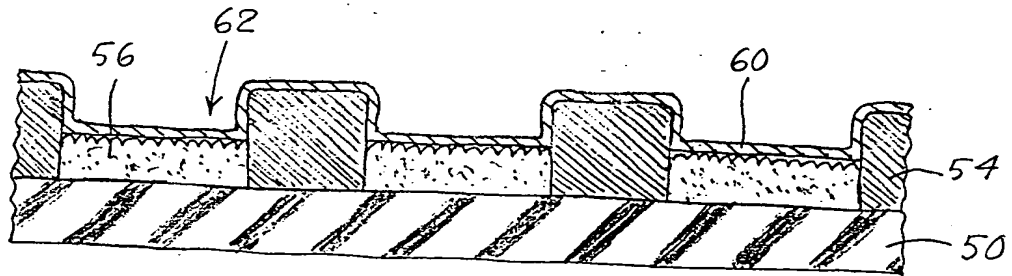


Fig. 18d

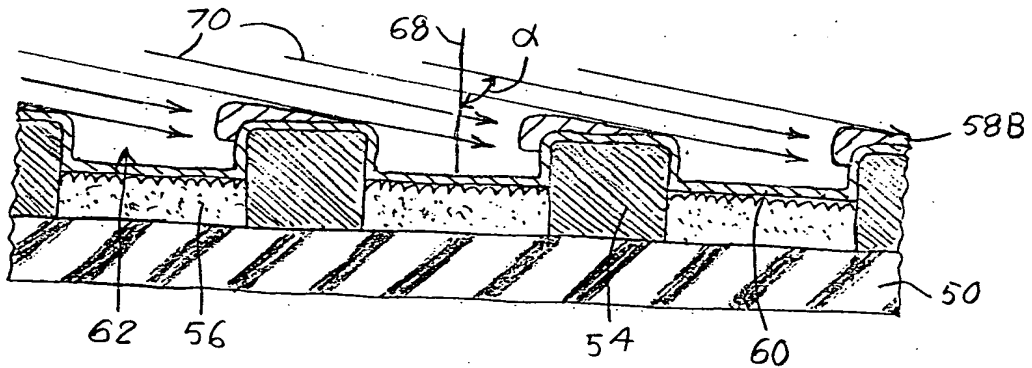
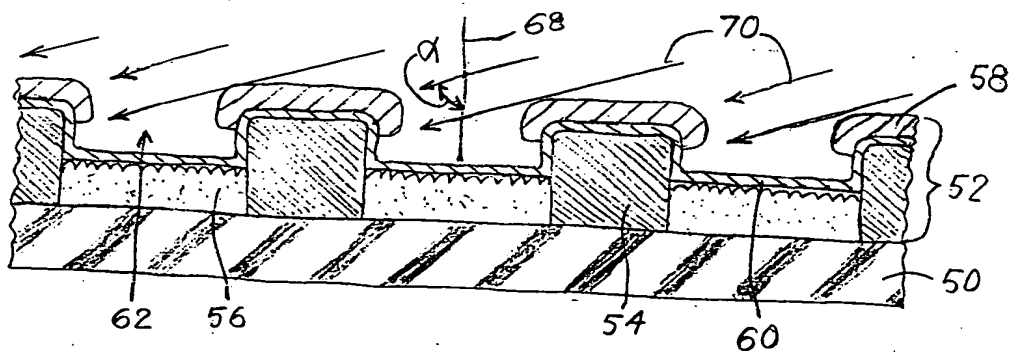
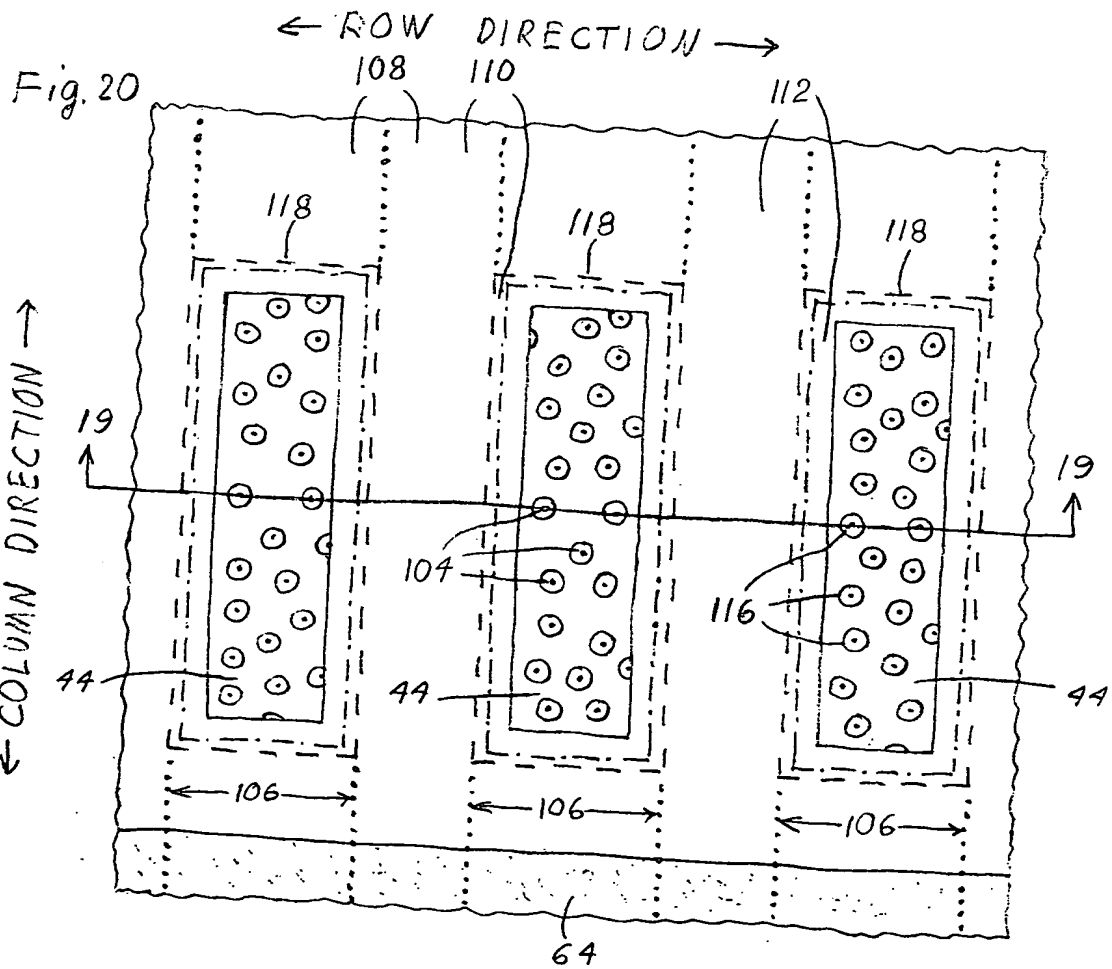
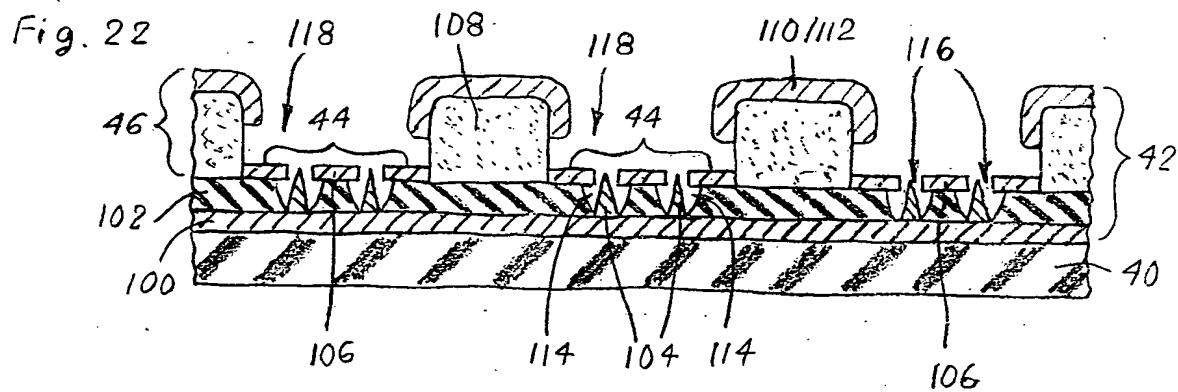
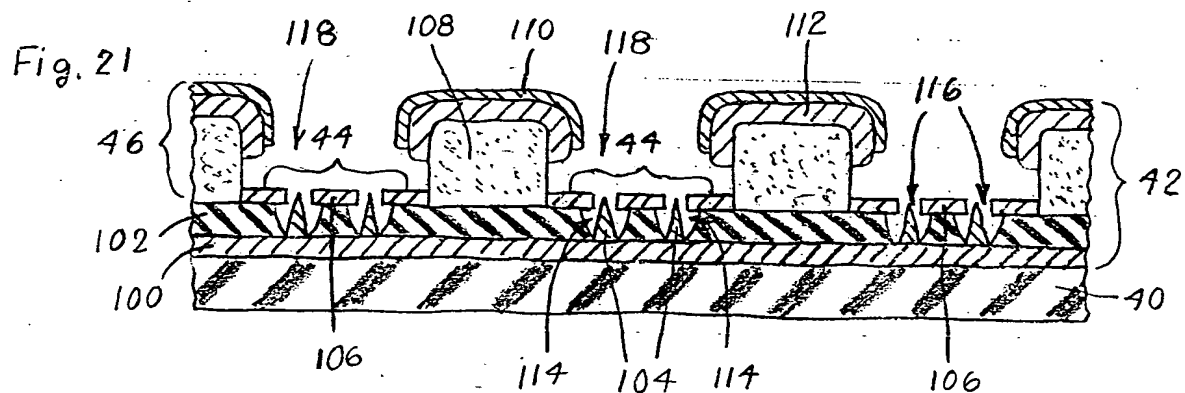


Fig. 18e



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[illegible]

A cross-sectional view of a semiconductor device. The top surface is tilted at an angle α relative to a vertical line 120. A series of parallel lines 122 represent light incident on the top surface. The device consists of a substrate 102 with a patterned layer 104 on top. Above 104 are several rectangular blocks 106, each topped with a smaller rectangular block 110. The top surface of the blocks 110 is labeled 112A. A layer 114 is located between the blocks 106. A layer 116 is located between the blocks 110. A layer 118 is located between the blocks 106 and the substrate 102. A layer 108 is located between the blocks 110 and the substrate 102.

[illegible]

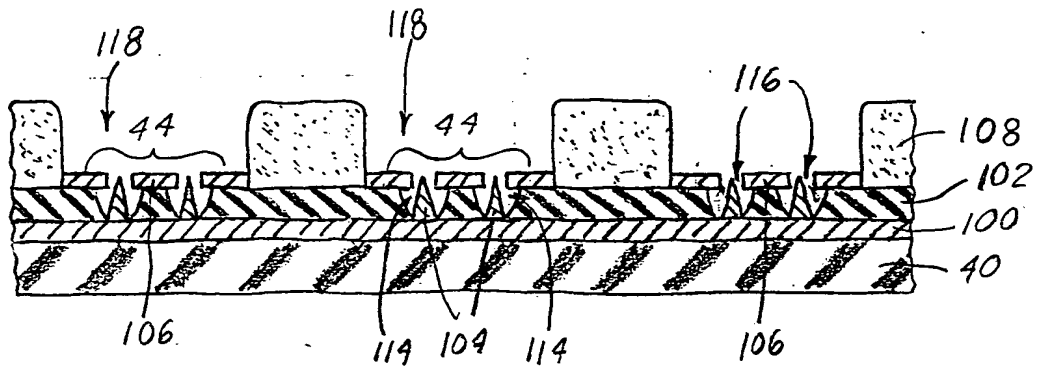
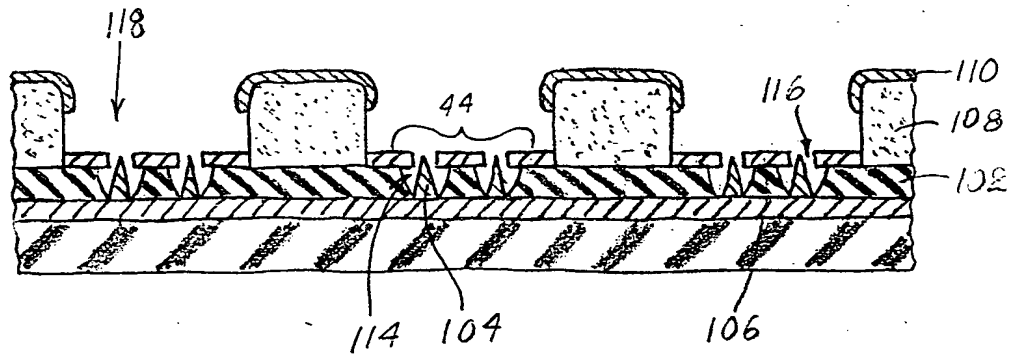
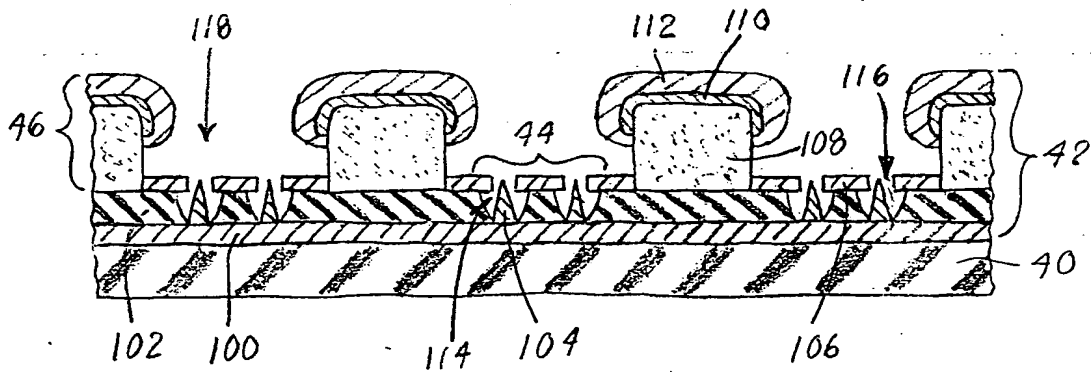
Fig.
24aFig.
24bFig.
24c

Fig.
25a

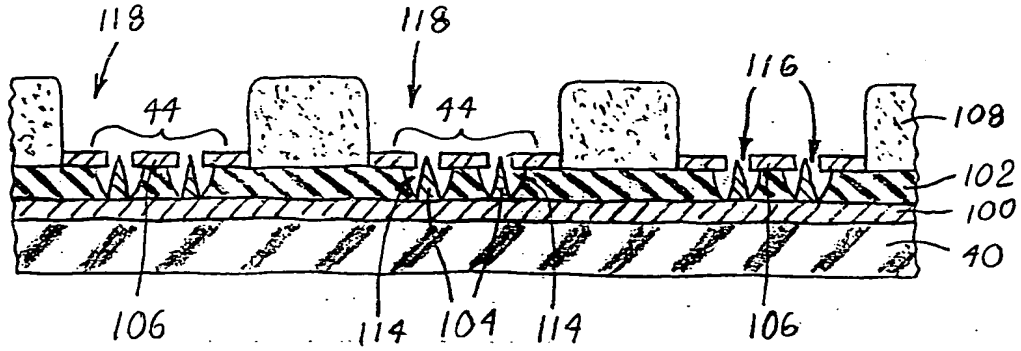


Fig.
25b

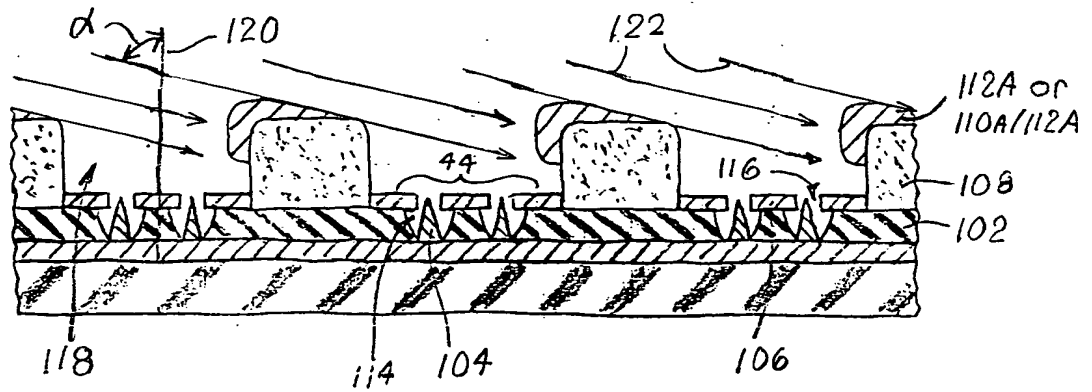


Fig.
25c

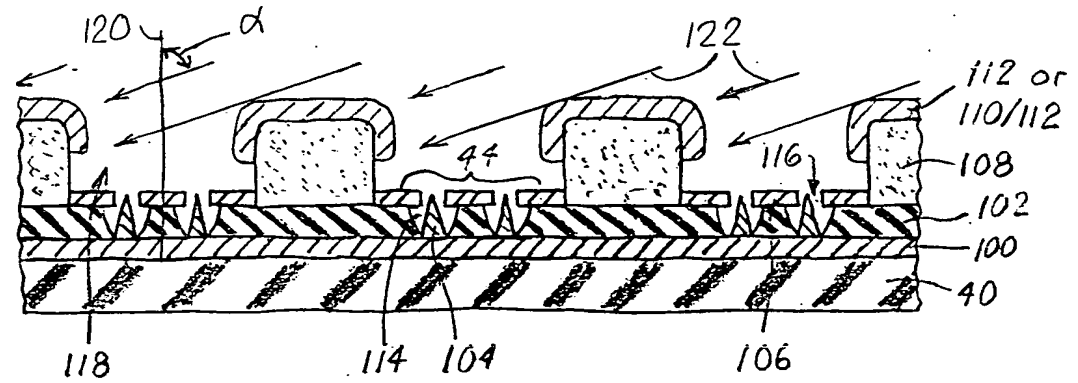
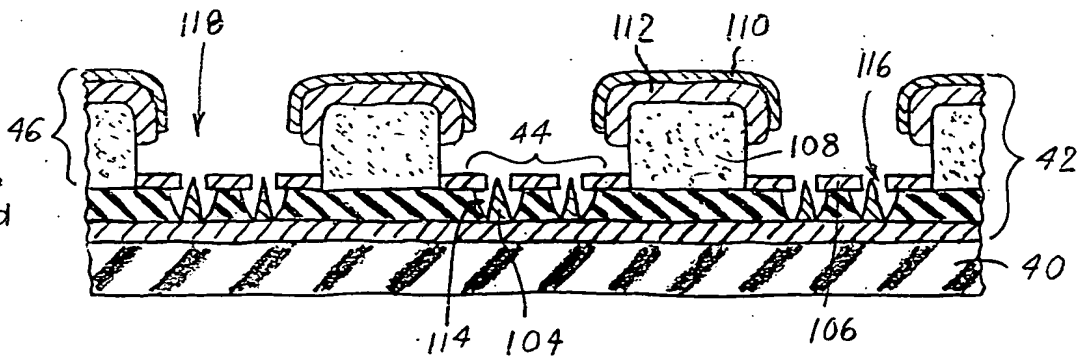


Fig.
25d



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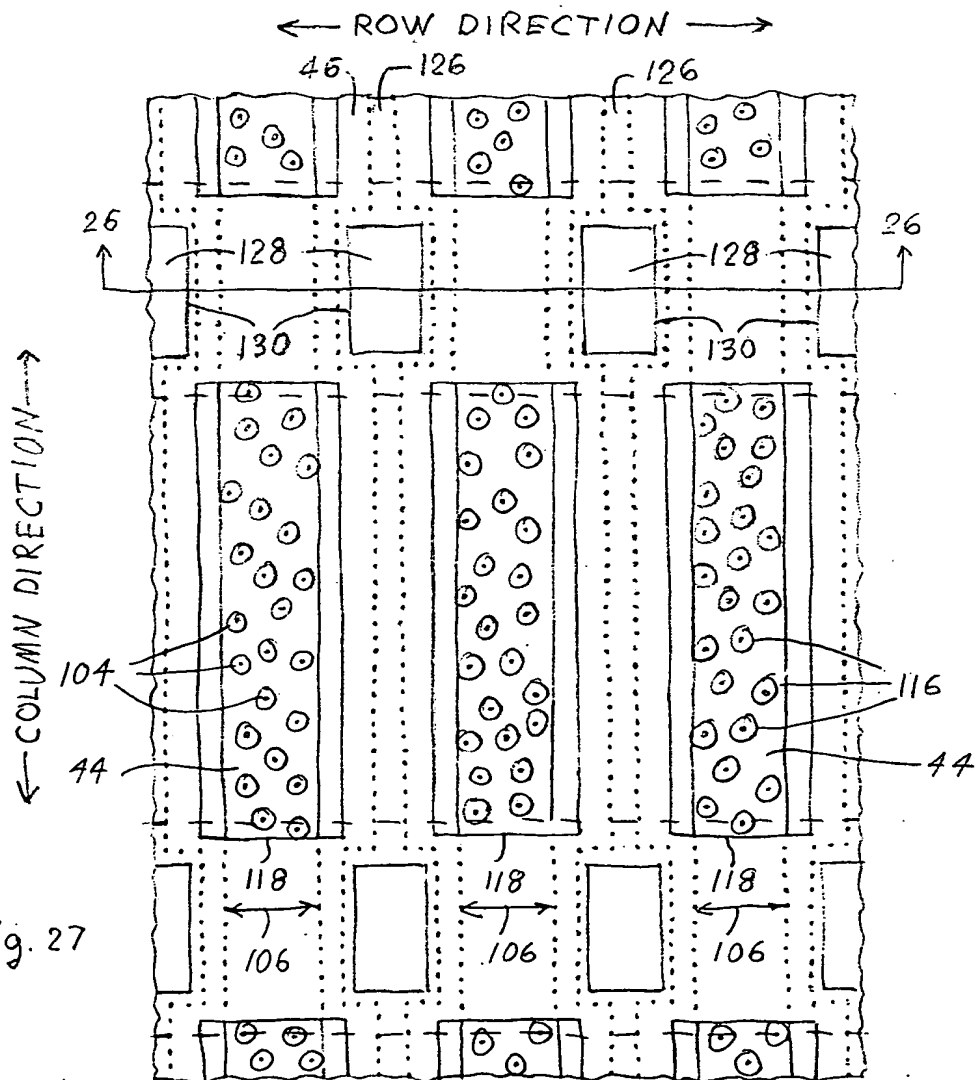
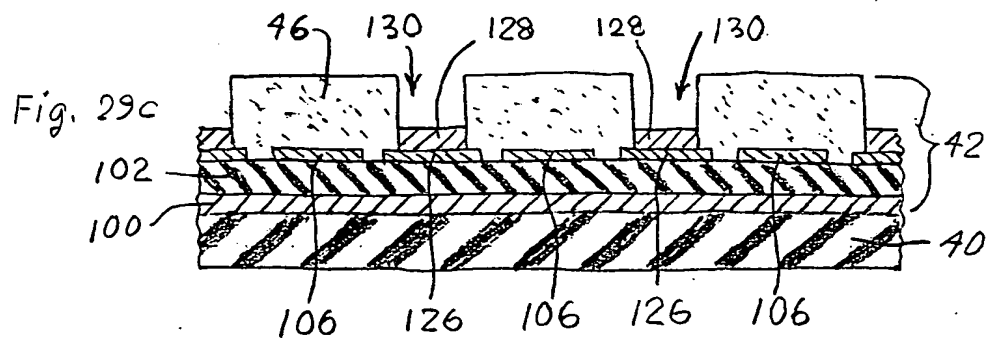
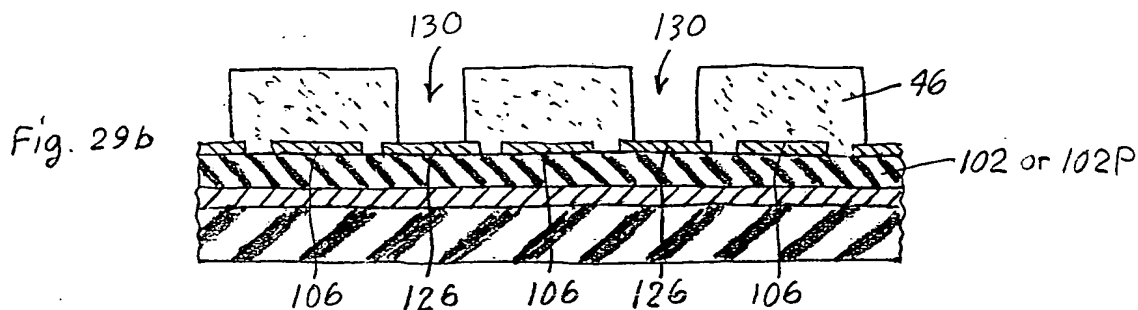
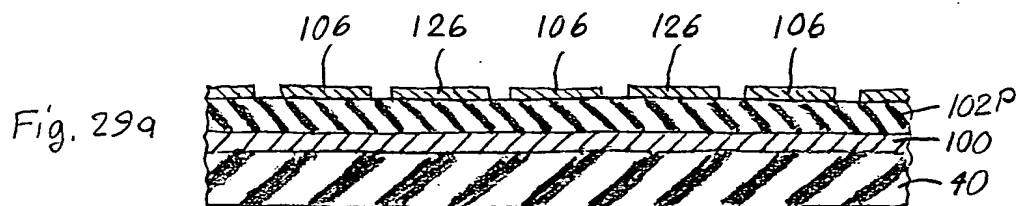
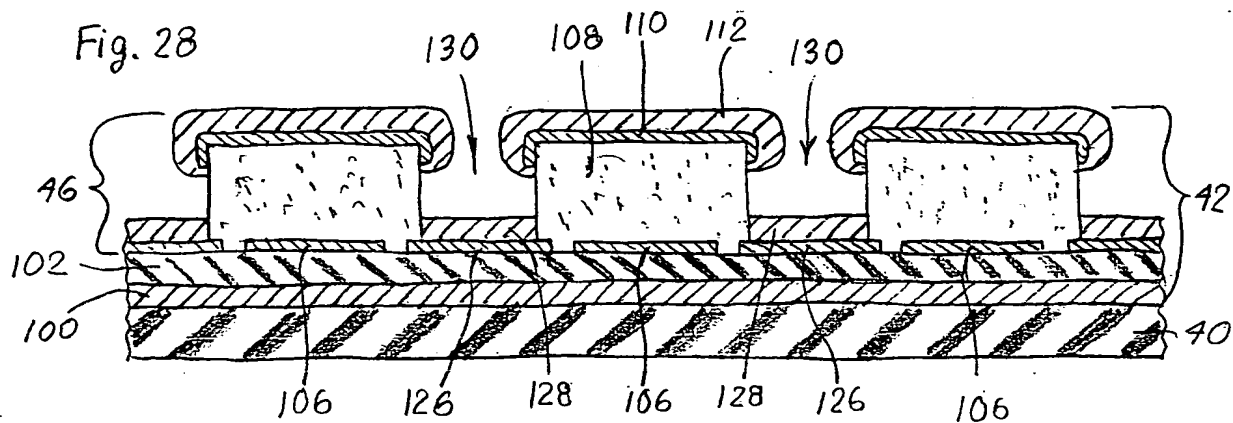


Fig. 27



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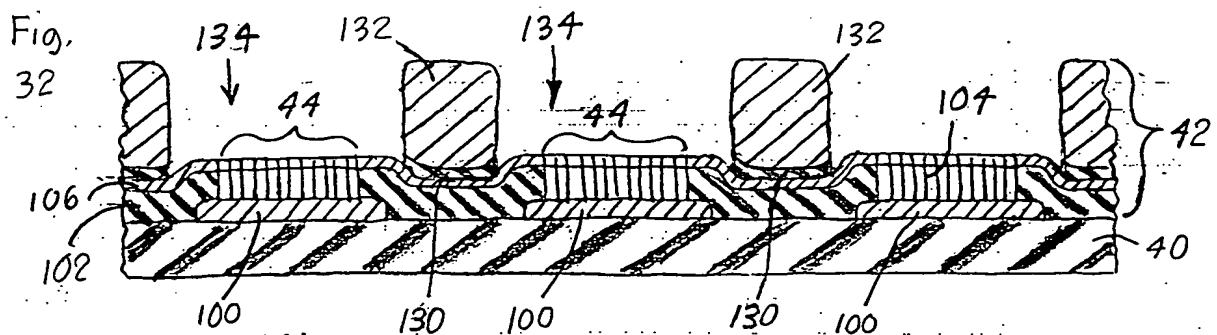
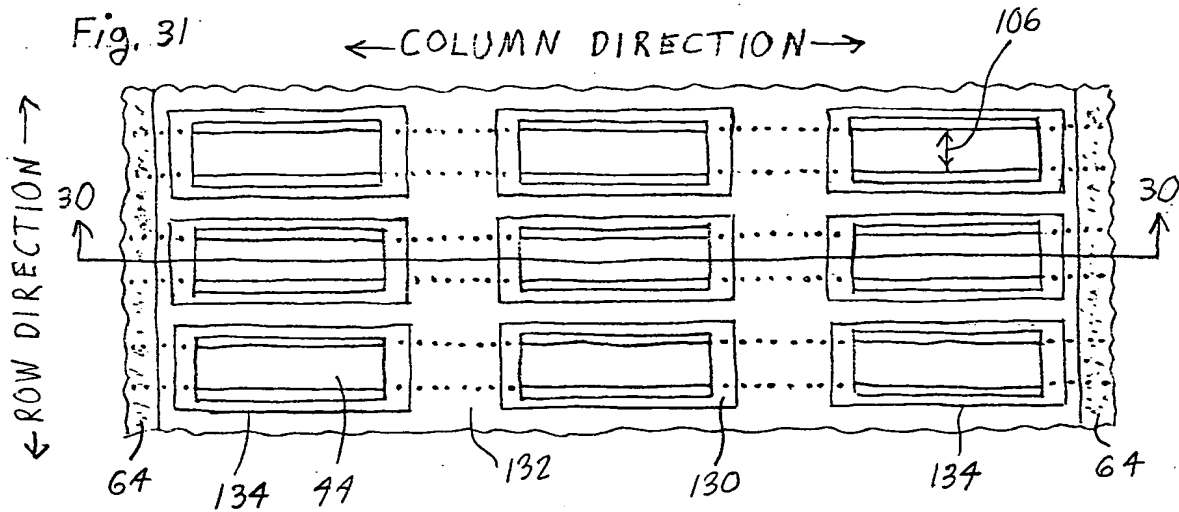
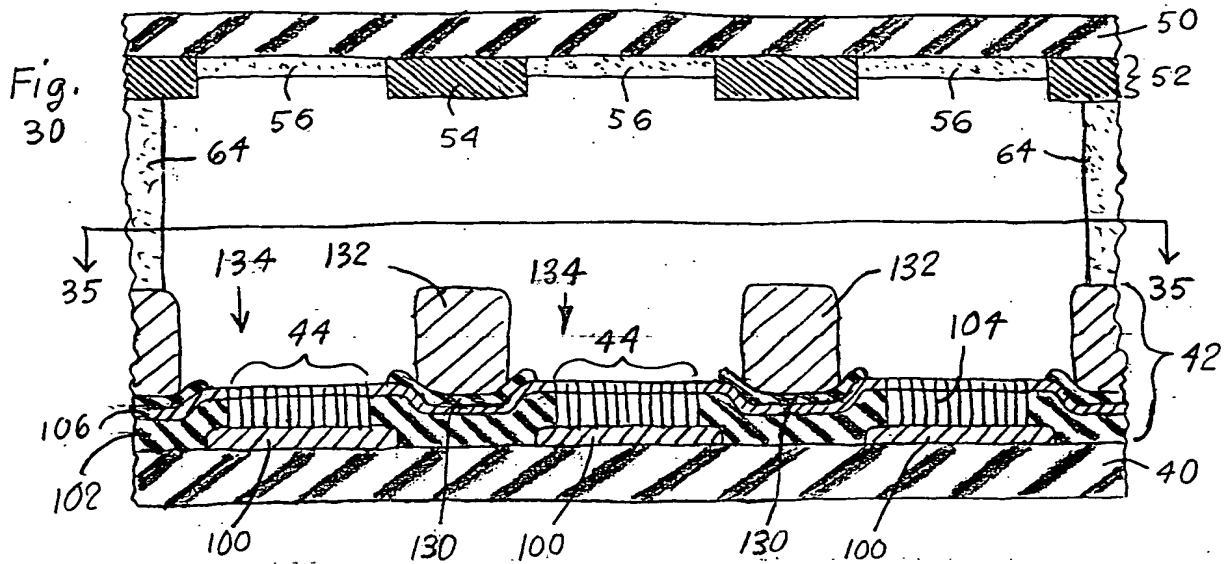


Fig.
33a

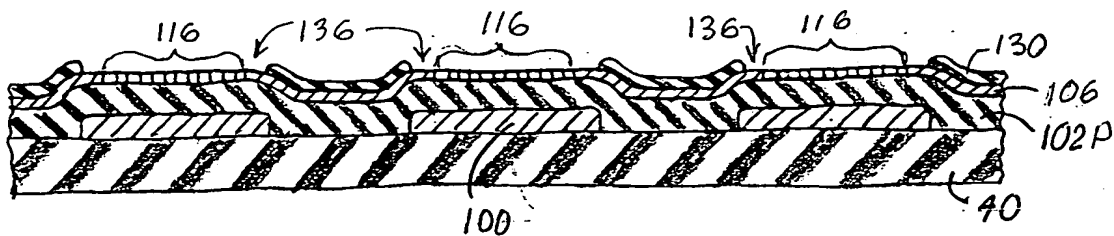


Fig.
33b

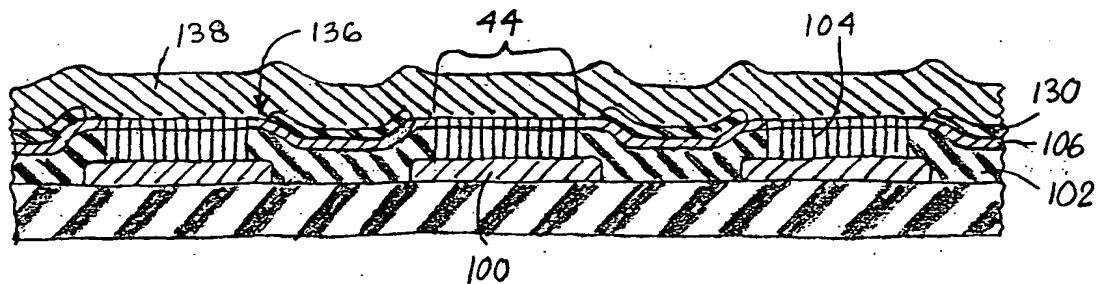


Fig.
33c

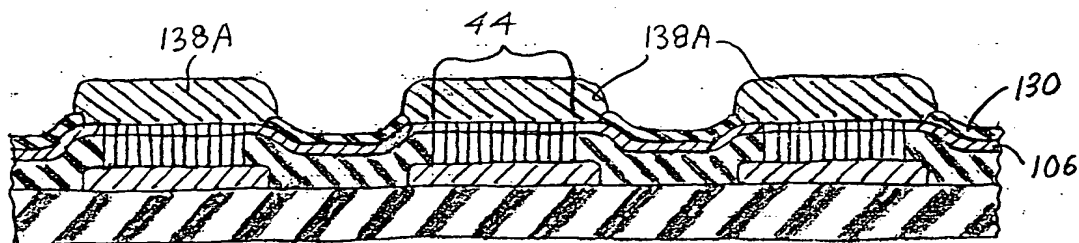


Fig.
33d

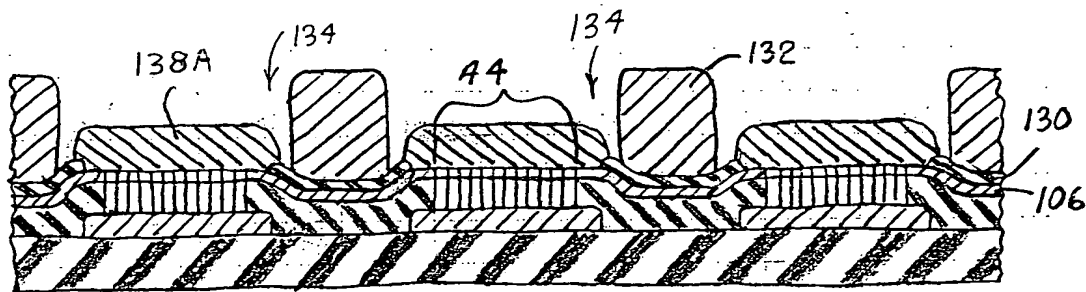
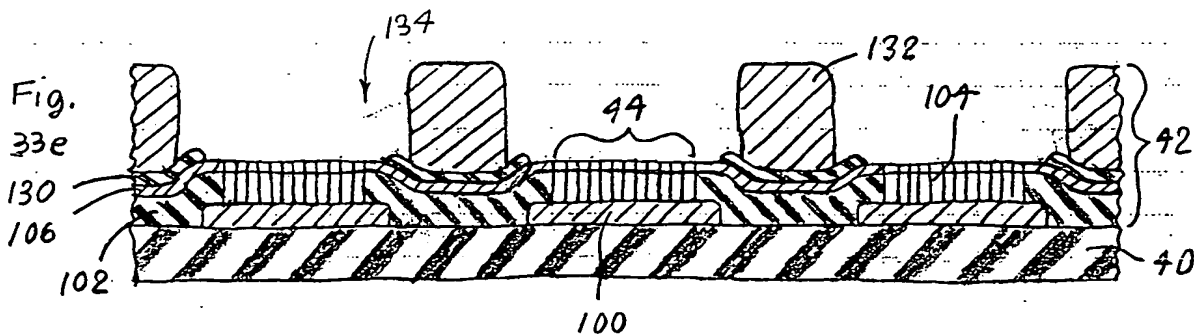
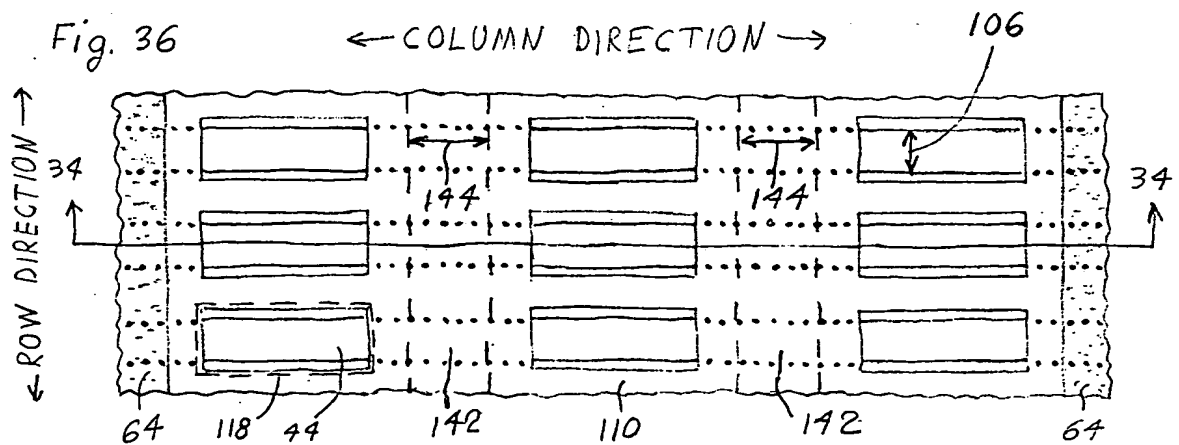
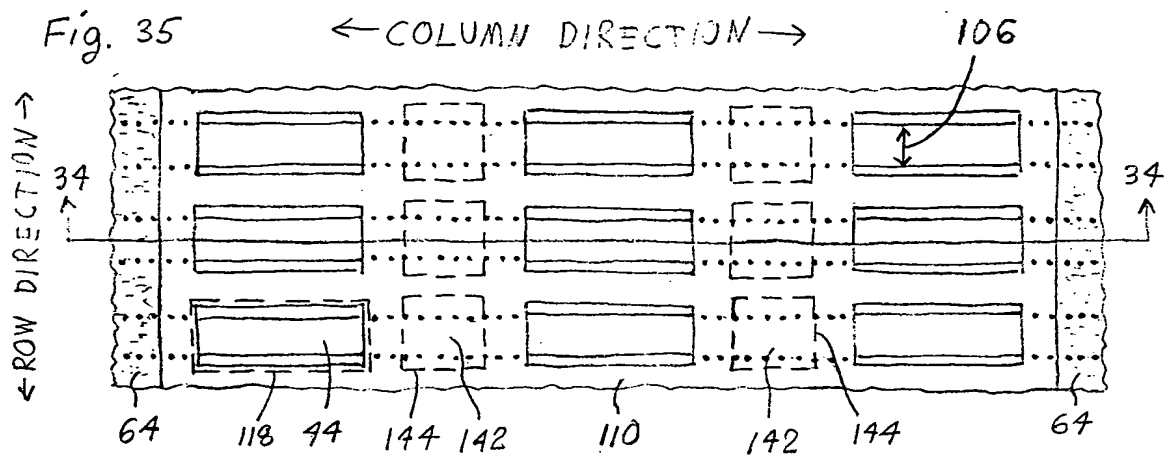
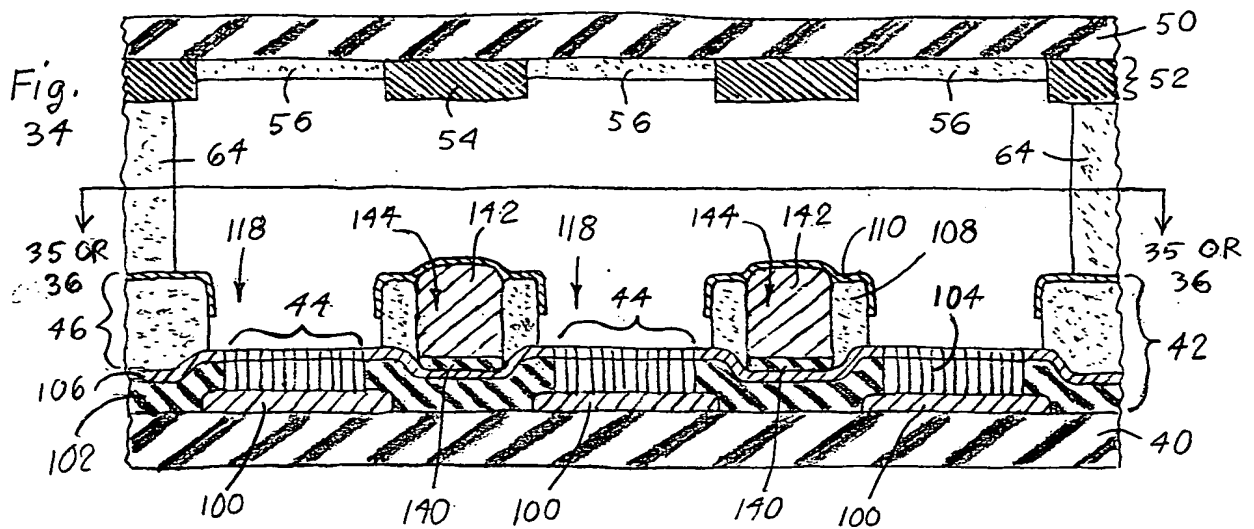
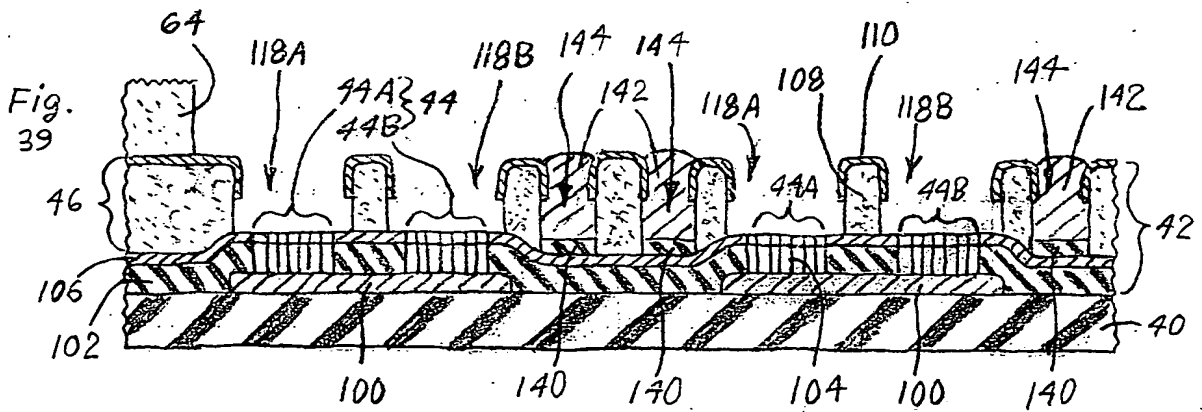
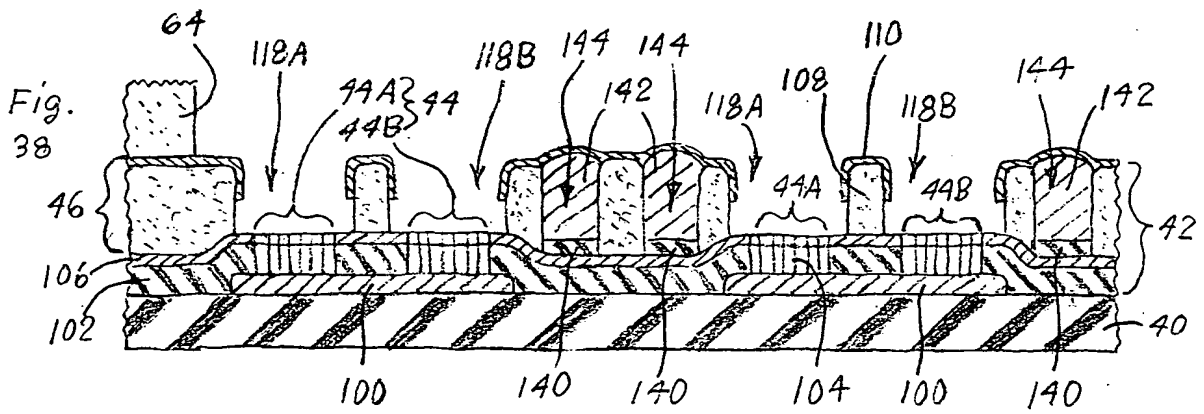
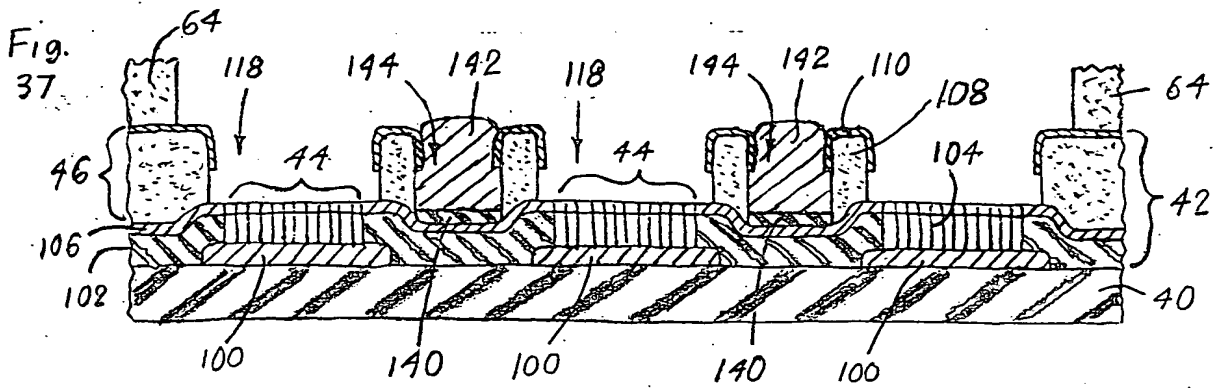


Fig.
33e

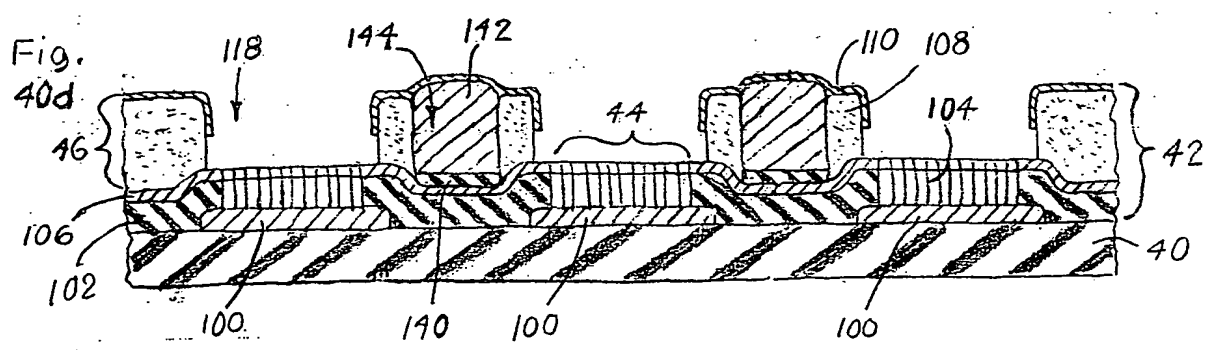
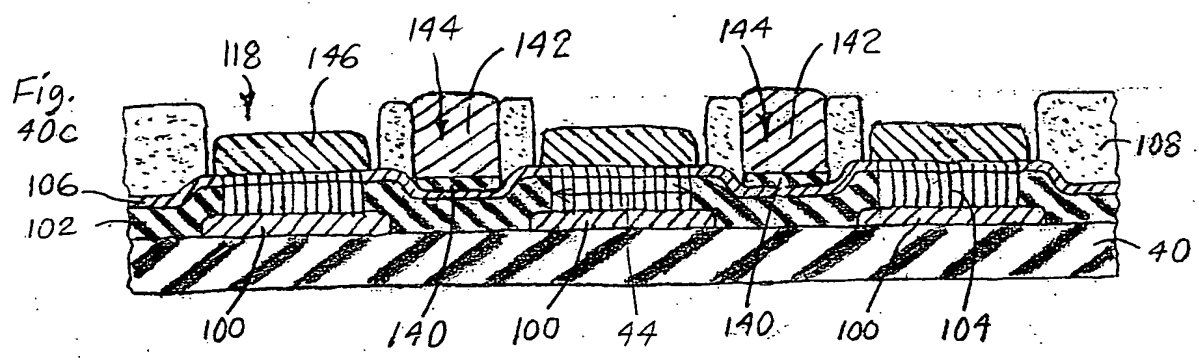
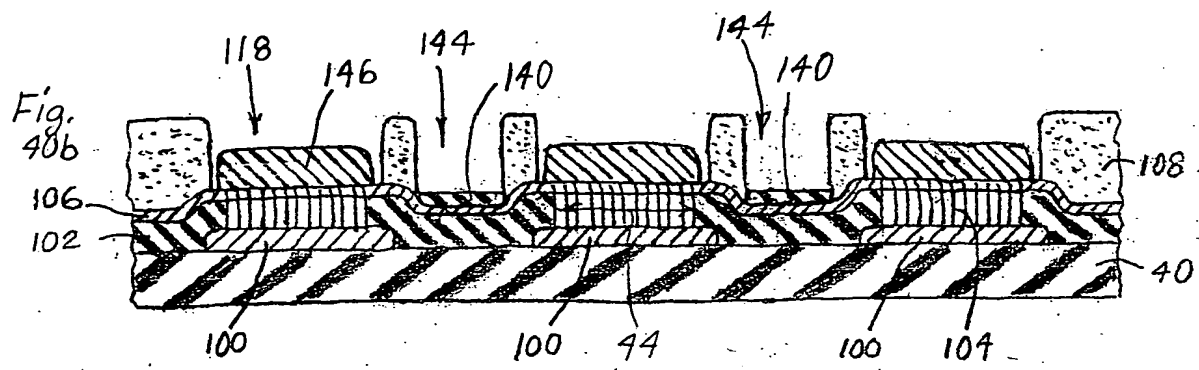
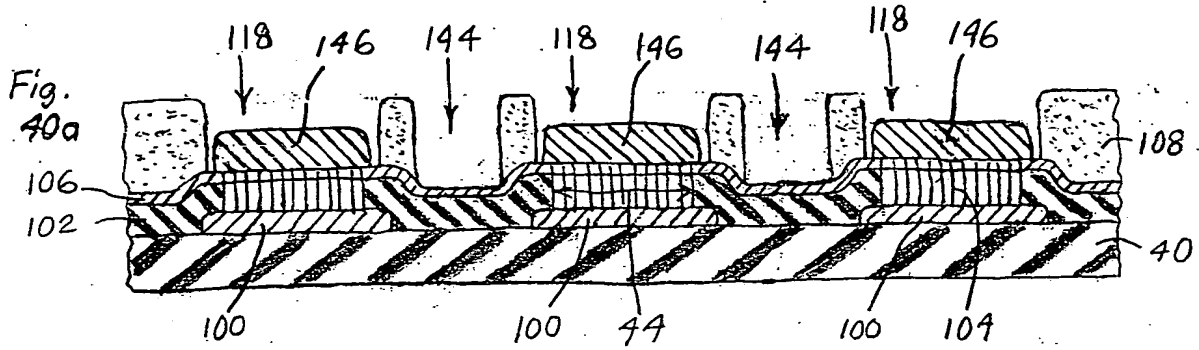


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